

NPN Darlington Transistor

PZTA29

Description

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from process 03.

Features

- These are Pb-Free Devices

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted) (Note 1, Note 2)

Symbol	Parameter	Value	Unit
V _{CE} S	Collector–Emitter Voltage	100	V
V _{CB} O	Collector–Base Voltage	100	V
V _{EB} O	Emitter–Base Voltage	12	V
I _C	Collector Current – Continuous	800	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to + 150	°C

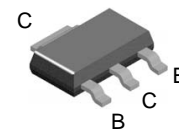
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are based on a maximum junction temperature of 150°C.
2. These are steady-state limits. **onsemi** should be consulted on application involving pulsed or low duty cycle operations.

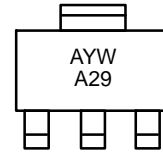
THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Max	Unit
P _D	Total Device Dissipation	1000	mW
	Derate Above 25°C	8.0	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient	125	°C/W

3. Device mounted on FR–4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6cm².



MARKING DIAGRAM



SOT–223
CASE 318H

A = Assembly Location
YW = Date Code
A29 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
PZTA29	SOT–223	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PZTA29

ELECTRICAL CHARACTERISTICS (Note 4) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Max	Unit
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OFF CHARACTERISTICS

$V_{(BR)CES}$	Collector–Emitter Breakdown Voltage	$I_C = 100\ \mu\text{A}$, $V_{BE} = 0$	100		V
$V_{(BR)CBO}$	Collector–Base Breakdown Voltage	$I_C = 100\ \mu\text{A}$, $I_E = 0$	100		V
$V_{(BR)EBO}$	Emitter–Base Breakdown Voltage	$I_E = 10\ \mu\text{A}$, $I_C = 0$	12		V
I_{CBO}	Collector Cut–Off Current	$V_{CB} = 80\ \text{V}$, $I_E = 0$		100	nA
I_{CES}	Collector Cut–Off Current	$V_{CE} = 80\ \text{V}$, $V_{BE} = 0$		500	nA
I_{EBO}	Emitter Cut–Off Current	$V_{EB} = 10\ \text{V}$, $I_C = 0$		100	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 10\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$	10,000		
		$I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$	10,000		
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage	$I_C = 10\ \text{mA}$, $I_B = 0.01\ \text{mA}$		1.2	V
		$I_C = 100\ \text{mA}$, $I_B = 0.1\ \text{mA}$		1.5	
$V_{BE(on)}$	Base–Emitter On Voltage	$I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$		2.0	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain Bandwidth Product	$I_C = 15\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$, $f = 100\ \text{MHz}$	125		MHz
C_{obo}	Output Capacitance	$V_{CB} = 1.0\ \text{V}$, $I_E = 0$, $f = 1.0\ \text{MHz}$		8.0	pF

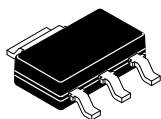
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2.0\%$.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

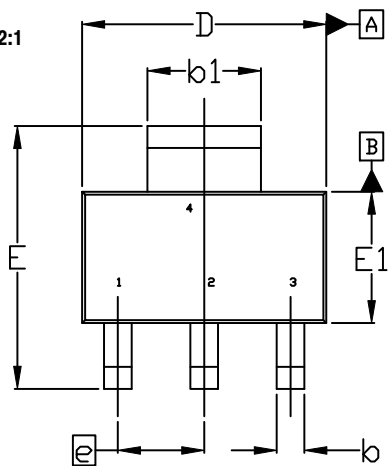
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SOT-223
CASE 318H
ISSUE B

DATE 13 MAY 2020

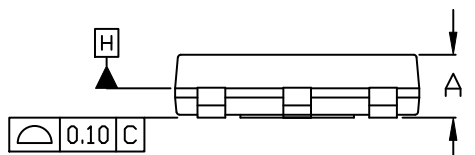
SCALE 2:1



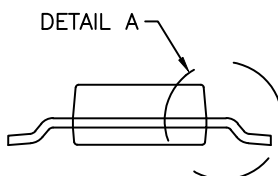
TOP VIEW

$\Phi 0.10 \text{ (M)}$ C A B

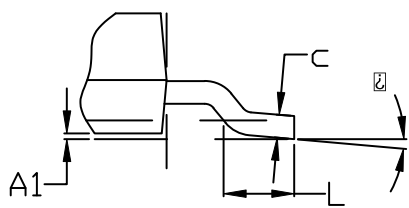
NOTE 7



SIDE VIEW



END VIEW

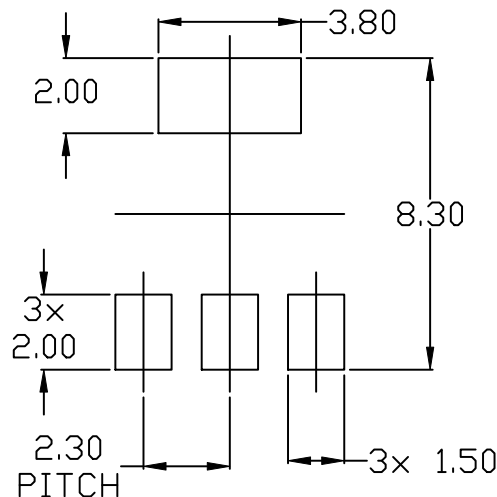


DETAIL A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
4. LEAD DIMENSIONS b AND b1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.08mm PER SIDE.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
7. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

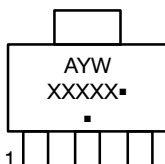
DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
A	---	---	1.80
A1	0.02	0.06	0.11
b	0.60	0.74	0.88
b1	2.90	3.00	3.10
c	0.24	---	0.35
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.30 BSC		
L	0.25	---	---
\square	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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